

# Digital Transistors (BRT) R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

NPN Transistors with Monolithic Bias Resistor Network

## MUN2213, MMUN2213L, MUN5213, DTC144EE, DTC144EM3, NSBC144EF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

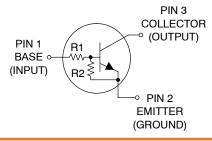
#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

Rating	Symbol	Max	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

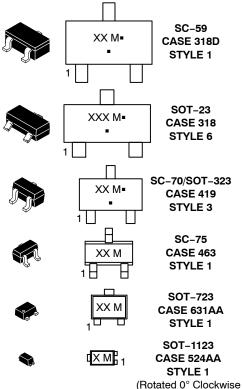
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

#### **PIN CONNECTIONS**



# MARKING DIAGRAMS



XXX = Specific Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

**Table 1. ORDERING INFORMATION** 

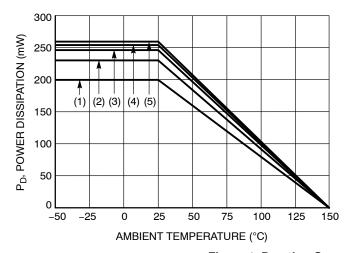
Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2213T1G, SMUN2213T1G*	8C	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2213LT1G, SMMUN2213LT1G*	A8C	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMUN2213LT3G	A8C	SOT-23 (Pb-Free)	10000 / Tape & Reel
MUN5213T1G, SMUN5213T1G*	8C	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC144EET1G, SDTC144EET1G*	8C	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC144EM3T5G, NSVDTC144EM3T5G*	8C	SOT-723 (Pb-Free)	8000 / Tape & Reel

#### **DISCONTINUED** (Note 1)

NSBC144EF3T5G	D	SOT-1123	8000 / Tape & Reel
		(Pb-Free)	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>1.</sup> **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on <a href="https://www.onsemi.com">www.onsemi.com</a>.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit			
THERMAL CHARACTERISTICS (SC-59) (MUN2213)							
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 2) (Note 3) (Note 2) (Note 3)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C			
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{ hetaJA}$	540 370	°C/W			
Thermal Resistance Junction to Lead	(Note 2) (Note 3)	$R_{ hetaJL}$	264 287	°C/W			
Junction and Storage Tem	Junction and Storage Temperature Range		-55 to +150	°C			

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERIST	ICS (SOT-23) (MMUN2213L)		•	
Total Device Dissipation $T_{A} = 25^{\circ}C$ (Note 3)	(Note 2)	P <sub>D</sub>	246 400	mW
Derate above 25°C (Note 3)	(Note 2)		2.0 3.2	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 3)	$R_{ hetaJA}$	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 2) (Note 3)	$R_{ hetaJL}$	174 208	°C/W
Junction and Storage Temper	rature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERIST	ICS (SC-70/SOT-323) (MUN5213)			
Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C	(Note 2) (Note 3) (Note 2) (Note 3)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{ hetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 2) (Note 3)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temper	rature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERIST	ICS (SC-75) (DTC144EE, SDTC144EE)	<u> </u>		
Total Device Dissipation		P <sub>D</sub>		
T <sub>A</sub> = 25°C Derate above 25°C	(Note 2) (Note 3) (Note 2) (Note 3)		200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temper	rature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERIST	ICS (SOT-723) (DTC144EM3)	j		
Total Device Dissipation	44.4.0	P <sub>D</sub>		,,,
T <sub>A</sub> = 25°C Derate above 25°C	(Note 2) (Note 3) (Note 2)		260 600 2.0	mW mW/°C
	(Note 3)		4.8	
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3)	$R_{ hetaJA}$	480 205	°C/W
Junction and Storage Temper	rature Range	$T_J$ , $T_{stg}$	-55 to +150	°C
THERMAL CHARACTERIST	ICS (SOT-1123) (NSBC144EF3)			
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 4) (Note 5)	$P_{D}$	254 297	mW
Derate above 25°C	(Note 4) (Note 5)		2.0 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 4)	$R_{ hetaJL}$	193	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 2. FR-4 @ Minimum Pad.
- 3. FR-4 @ 1.0 x 1.0 Inch Pad.
- 4. FR-4 @ 100 mm², 1 oz. copper traces, still air.
  5. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•	•	
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	0.1	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \mu A, I_E = 0)$	V <sub>(BR)</sub> CBO	50	-	_	Vdc
Collector–Emitter Breakdown Voltage (Note 6) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	_	Vdc
ON CHARACTERISTICS	-				
DC Current Gain (Note 6) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	140	_	
Collector–Emitter Saturation Voltage (Note 6) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	V <sub>CE(sat)</sub>	-	-	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	-	1.2	0.8	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_{C} = 2.0 \text{ mA})$	V <sub>i(on)</sub>	3.0	1.6	_	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 3.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	-	_	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle < 2%.

# TYPICAL CHARACTERISTICS MUN2213, MMUN2213L, MUN5213, DTC144EE, SDTC144EE, DTC144EM3

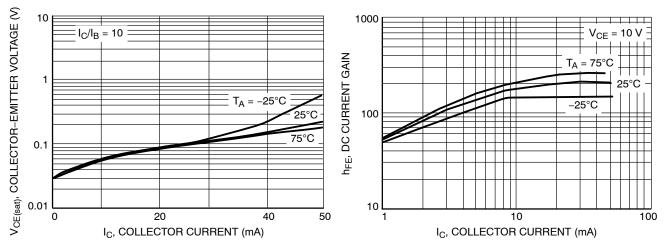


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

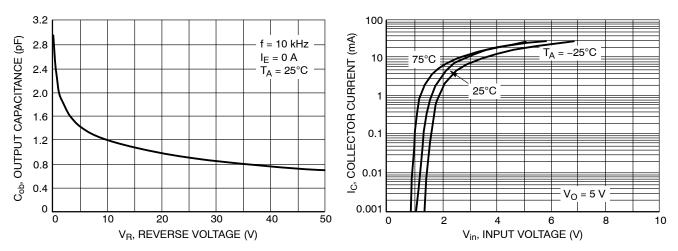


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

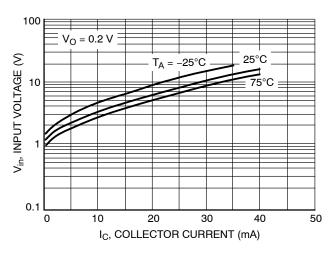


Figure 6. Input Voltage vs. Output Current

#### **TYPICAL CHARACTERISTICS - NSBC144EF3**

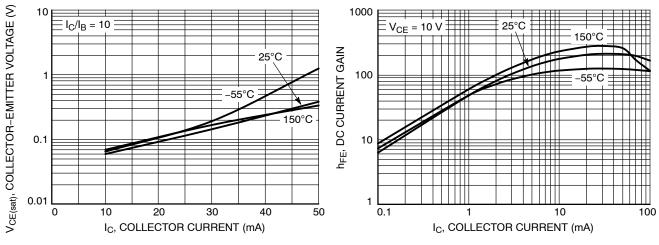


Figure 7.  $V_{CE(sat)}$  vs.  $I_{C}$ 

Figure 8. DC Current Gain

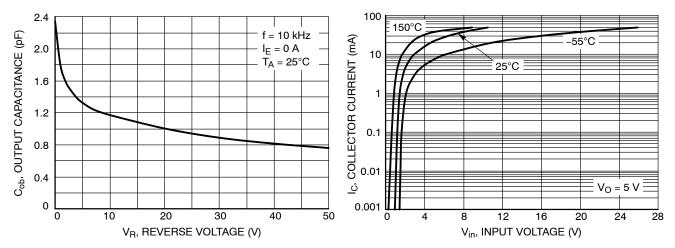


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

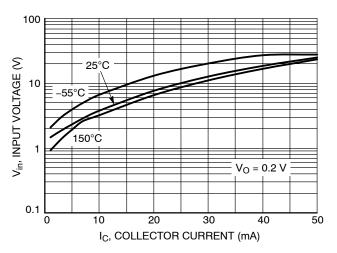


Figure 11. Input Voltage vs. Output Current

#### **PACKAGE DIMENSIONS**



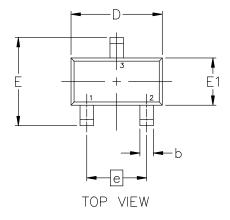
SC-59-3 2.90x1.50x1.15, 1.90P CASE 318D **ISSUE J** 

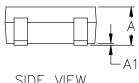
**DATE 15 FEB 2024** 

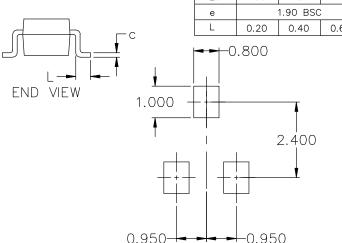
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

	MILLIMETERS				
DIM	MIN.	NOM.	MAX.		
Α	1.00	1.15	1.30		
A1	0.01	0.06	0.10		
Ф	0.35	0.43	0.50		
C	0.09	0.14	0.18		
D	2.70	2.90	3.10		
E	2.50	2.80	3.00		
E1	1.30	1.50	1.70		
е	1.90 BSC				
L	0.20	0.40	0.60		

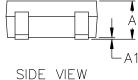






#### RECOMMENDED MOUNTING FOOTPRINT\*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



**GENERIC MARKING DIAGRAM\*** 



XXX = Specific Device Code

= Date Code M

= Pb-Free Package\*

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. ANODE PIN 1. ANODE 2. EMITTER 2. N.C. 3. CATHODE 3. CATHODE 3. COLLECTOR

STYLE 4: PIN 1. CATHODE STYLE 5: STYLE 6: PIN 1. CATHODE PIN 1. ANODE 2. CATHODE 2. N.C. 2 CATHODE 3. ANODE 3. ANODE/CATHODE

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_





#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

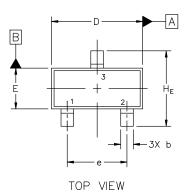
2.04

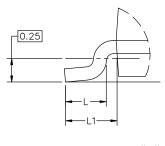
0.55

0.69

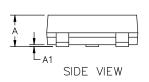
2.64

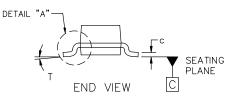
10°





DETAIL "A" Scale 3:1





## 2.90 3X 0.95 3X 0.56 -0.95 PITCH

#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package



\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 1 OF 2

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

## SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	







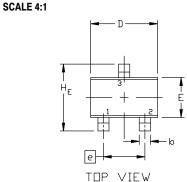
SC-70 (SOT-323) CASE 419 ISSUE R

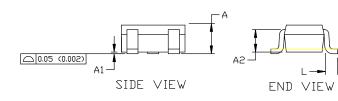
**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





# GENERIC MARKING DIAGRAM

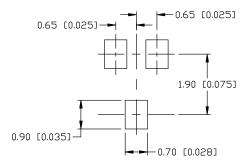


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1



#### SC75-3 1.60x0.80x0.80, 1.00P

**CASE 463 ISSUE H** 

**DATE 01 FEB 2024** 

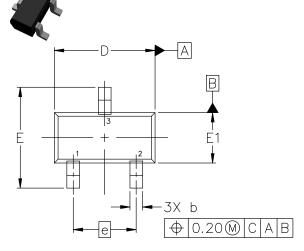
#### NOTES:

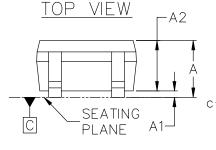
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

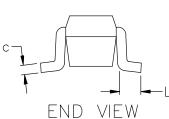
DIM	MILLIMETERS			
DIM	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	0.80 REF.			
b	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
Е	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	

-0.356

0.787







SIDE VIEW

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3 CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3 CATHODE

SC75-3 1.60x0.80x0.80, 1.00P

RECOMMENDED MOUNTING FOOTPRINT\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES

1.803

0.508

REFERENCE MANUAL, SOLDERRM/D.

1.000

STYLE 4:	STYLE 5:
PIN 1. CATHODE	PIN 1. GATE
2. CATHODE	2. SOURCE
3. ANODE	3. DRAIN

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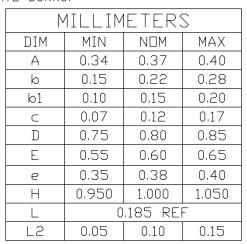


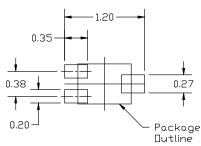
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3, MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



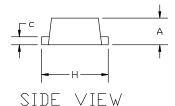


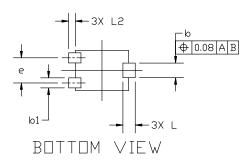
# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□LDERRM/D.

# D A B

TOP VIEW





# GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE
PIN 1. BASE	PIN
2. EMITTER	
<ol><li>COLLECTOR</li></ol>	:

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE

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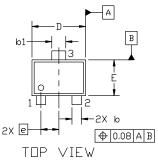


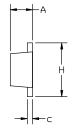
#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

**DATE 24 JAN 2024** 

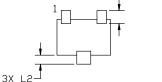
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



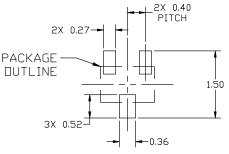






BOTTOM VIEW

#### MILLIMETERS DIM MIN. $N\square M$ . MAX. 0.45 0.50 0.55 Α 0.15 0.21 0.27 b b1 0.25 0.31 0.37 0.07 0.12 0.17 $\subset$ D 1.25 1.15 1.20 Ε 0.75 0.80 0.85 0.40 BSC е Н 1.20 1.25 1.15 0.29 REF L L2 0.15 0.20 0.25



# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

# GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	<ol><li>CATHODE</li></ol>	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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<u>DTC144EET1G DTC144EM3T5G NSBC144EF3T5G SMMUN2213LT1G SMUN5213T1G SMMUN2213LT3G SMUN2213T1G SDTC144EET1G NSVDTC144EM3T5G</u>